

印章/Marking: 2L

特点/Features:

击穿电压高;

用途/Applications:

用于普通高压放大, 与 MMBT5551 互补。



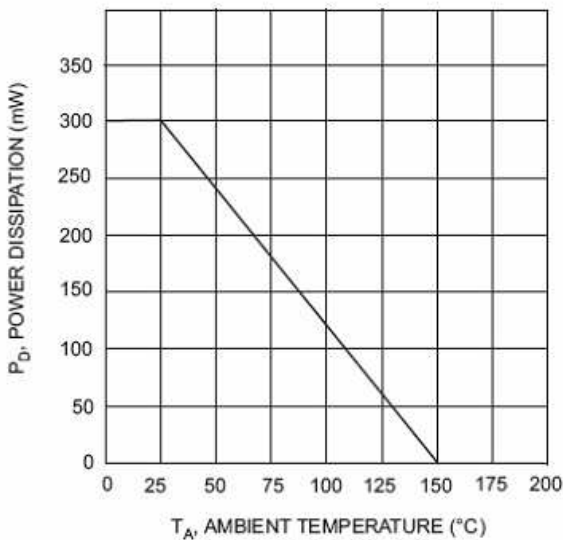
极限参数/Absolute maximum ratings ($T_a=25^{\circ}\text{C}$)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CB0}	-160	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CE0}	-150	V
发射极-基极电压/Emitter-Base Voltage	V_{EB0}	-5	V
集电极连续电流/Collector Current Continuous	I_C	-0.6	A
集电极耗散功率/Collector Power Dissipation	P_C	0.3	W
结温/Junction Temperature	T_j	150	$^{\circ}\text{C}$
储存温度/Storage Temperature	T_{stg}	-55~150	$^{\circ}\text{C}$

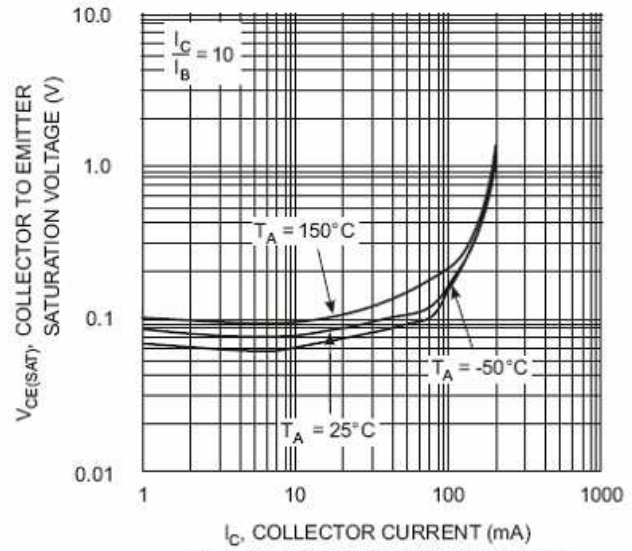
电性能参数/Electrical characteristics ($T_a=25^{\circ}\text{C}$)

参数	符号	测试条件	最小值	最大值	单位
集电极-基极击穿电压	$V_{BR(CB0)}$	$I_C=-100\mu\text{A}, I_E=0$	-160		V
集电极-发射极击穿电压	$V_{BR(CE0)}$	$I_C=-1\text{mA}, I_B=0$	-150		V
发射极-基极击穿电压	$V_{BR(EB0)}$	$I_E=-10\mu\text{A}, I_C=0$	-5		V
集电极截止电流	I_{CB0}	$V_{CB}=-120\text{V}, I_E=0$		-0.1	μA
发射极截止电流	I_{EB0}	$V_{EB}=-4\text{V}, I_C=0$		-0.1	μA
直流电流增益	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	80		
直流电流增益	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100	300	
直流电流增益	$h_{FE(3)}$	$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50		
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.5	V
基极-发射极饱和压降	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-1	V
特征频率	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=30\text{MHz}$	100		MHz

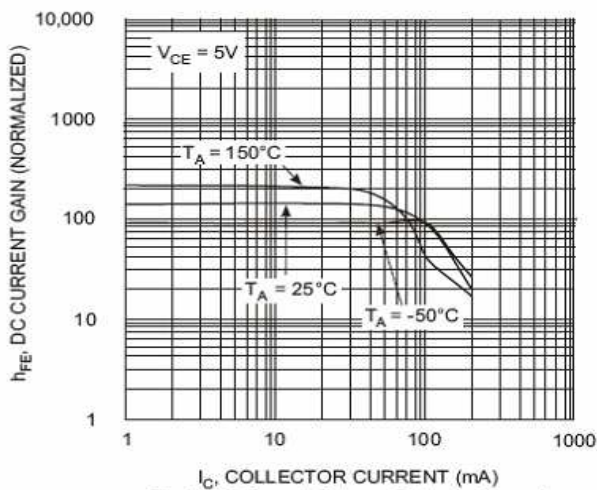
典型特性曲线图/Typical Characteristics



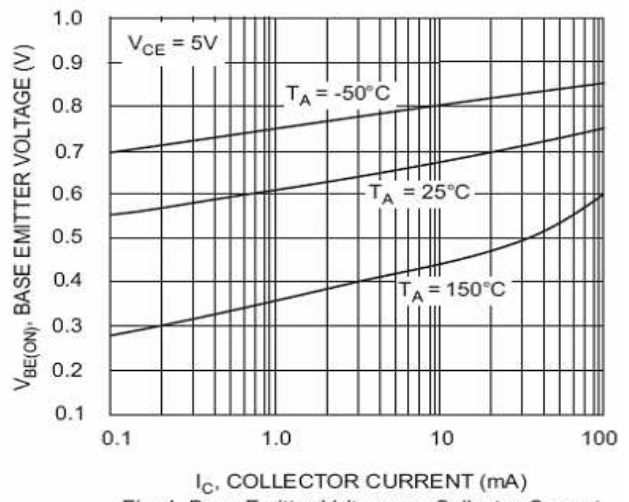
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1. Max Power Dissipation vs Ambient Temperature



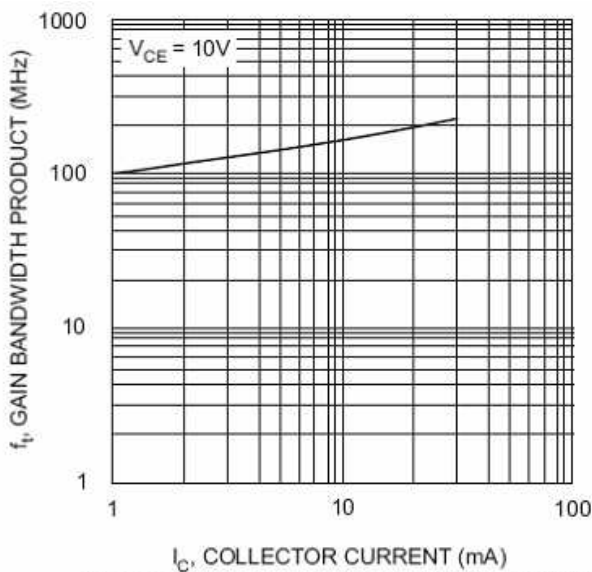
I_C , COLLECTOR CURRENT (mA)
Fig. 2. Collector Emitter Saturation Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 3. DC Current Gain vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 4. Base Emitter Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 5. Gain Bandwidth Product vs Collector Current